10-FY12PMA025I7-P588A98
datasheet

***flow*PIM 1** **1200 V / 25 A**

Topology features

- Kelvin Emitter for improved switching performance
- Open Emitter configuration
- Temperature sensor
- Converter+Brake+Inverter

Component features

- Easy paralleling
- Low collector emitter saturation voltage
- Low turn-off losses
- Positive temperature coefficient

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Thermo-mechanical push-and-pull force relief
- Solder pin

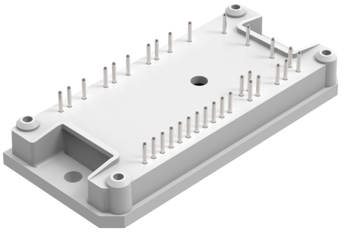
Target applications

- Industrial Drives

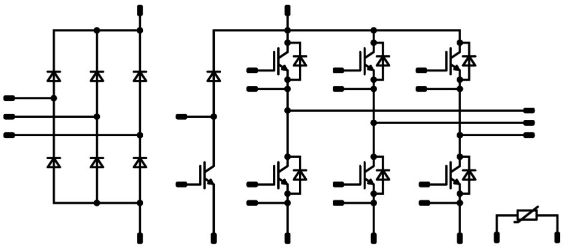
Types

- 10-FY12PMA025I7-P588A98

flow 1 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Inverter Switch					
Collector-emitter voltage	V_{CES}			1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	34	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		50	A
Turn off safe operating area		T_j = 150°C, V_{CE} = 1200 V		50	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	77	W
Gate-emitter voltage	V_{GES}			±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 800 V	T_j = 175 °C	7	µs
Maximum junction temperature	T_{jmax}			175	°C
Inverter Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	26	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		42	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	49	W
Maximum junction temperature	T_{jmax}			175	°C
Brake Switch					
Collector-emitter voltage	V_{CES}			1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	24	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		30	A
Turn off safe operating area		T_j = 150°C, V_{CE} = 1200 V		30	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	58	W
Gate-emitter voltage	V_{GES}			±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V,	T_j = 175 °C	7	µs
Maximum junction temperature	T_{jmax}			175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Brake Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	18	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		22	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	35	W
Maximum junction temperature	T_{jmax}			175	°C
Rectifier Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	44	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	270	A
Surge current capability	I^2t			370	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	56	W
Maximum junction temperature	T_{jmax}			150	°C

Module Properties

Parameter	Symbol	Conditions		Value	Unit
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage	t_p = 1 min	2500	V
Creepage distance				>12,7	mm
Clearance				7,91	mm
Comparative Tracking Index	CTI			≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00053	25	5,15	5,8	6,45	V
Collector-emitter saturation voltage	V_{CEsat}		15		25	25 125 150	1,35	1,6 1,78 1,83	1,75(1)	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			5,6	µA
Gate-emitter leakage current	I_{GES}		20	0		25			100	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 100 kHz	0	25		25		4800		pF
Reverse transfer capacitance	C_{res}	f = 100 kHz	0	25		25		17		pF
Gate charge	Q_g	V_{CC} = 600 V	±15		25	25		395		nC
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,24		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 8 Ω R_{goff} = 8 Ω	±15	600	25	25 125 150		104 106,21 107,12		ns
Rise time	t_r	R_{gon} = 8 Ω R_{goff} = 8 Ω	±15	600	25	25 125 150		23,15 26,59 27,21		ns
Turn-off delay time	$t_{d(off)}$	R_{gon} = 8 Ω R_{goff} = 8 Ω	±15	600	25	25 125 150		182,48 242,25 256,53		ns
Fall time	t_f	R_{gon} = 8 Ω R_{goff} = 8 Ω	±15	600	25	25 125 150		115,14 185,65 206,44		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=1,43 µC Q_{rFWD}=2,86 µC Q_{rFWD}=3,31 µC	±15	600	25	25 125 150		1,35 1,86 2,02		mWs
Turn-off energy (per pulse)	E_{off}		±15	600	25	25 125 150		1,62 2,57 2,84		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Diode										
Static										
Forward voltage	V_F				21	25 125 150	1,55	1,8 1,72 1,69	2(1)	V
Reverse leakage current	I_R	V_r = 1200 V				25			0,27	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,95		K/W
Dynamic										
Peak recovery current	I_{RM}	d*i*/d*t*=1058 A/µs d*i*/d*t*=1018 A/µs d*i*/d*t*=990 A/µs	±15	600	25	25 125 150		19,7 27,57 29,72		A
Reverse recovery time	t_{rr}					25 125 150		177,99 268,06 299,2		ns
Recovered charge	Q_r					25 125 150		1,43 2,86 3,31		µC
Reverse recovered energy	E_{rec}					25 125 150		0,518 1,1 1,29		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		635,28 140,5 149,9		A/µs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Brake Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00033	25	5,15	5,8	6,45	V
Collector-emitter saturation voltage	V_{CEsat}		15		15	25 125 150	1,35	1,56 1,74 1,8	1,75(1)	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			4,9	μA
Gate-emitter leakage current	I_{GES}		20	0		25			100	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 100 kHz	0	25		25		2800		pF
Reverse transfer capacitance	C_{res}	f = 100 kHz	0	25		25		10,4		pF
Gate charge	Q_g		±15	600	15	25		234		nC
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,64		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	0/15	700	15	25 125 150		33,53 32,92 32,49		ns
Rise time	t_r	R_{gon} = 16 Ω R_{goff} = 16 Ω	0/15	700	15	25 125 150		20,07 22,04 22,72		ns
Turn-off delay time	$t_{d(off)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	0/15	700	15	25 125 150		251,83 312,4 328,27		ns
Fall time	t_f	R_{gon} = 16 Ω R_{goff} = 16 Ω	0/15	700	15	25 125 150		87,56 158,39 182,84		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,795 μC Q_{rFWD}=1,64 μC Q_{rFWD}=1,92 μC	0/15	700	15	25 125 150		1,05 1,51 1,63		mWs
Turn-off energy (per pulse)	E_{off}		0/15	700	15	25 125 150		1,04 1,62 1,79		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Diode										
Static										
Forward voltage	V_F				11	25 125 150	1,55	1,78 1,66 1,63	2[(1)]	V
Reverse leakage current	I_R	V_r = 1200 V				25			0,2	µA
Thermal										
Thermal resistance junction to sink [(2)]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,69		K/W
Dynamic										
Peak recovery current	I_{RM}	d*i*/d*t*=737 A/µs d*i*/d*t*=652 A/µs d*i*/d*t*=616 A/µs	0/15	700	15	25 125 150		10,51 12,78 13,46		A
Reverse recovery time	t_{rr}					25 125 150		179,96 280,68 312,96		ns
Recovered charge	Q_r					25 125 150		0,795 1,64 1,92		µC
Reverse recovered energy	E_{rec}					25 125 150		0,314 0,708 0,836		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		233,98 34,42 35,05		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Rectifier Diode										
Static										
Forward voltage	V_F				28	25 125 150		1,15 1,11 1,1	1,5[1]	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 1000	µA
Thermal										
Thermal resistance junction to sink [2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,25		K/W
Thermistor										
Static										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %						4000		K
Vincotech Thermistor Reference									I	

(1) Value at chip level

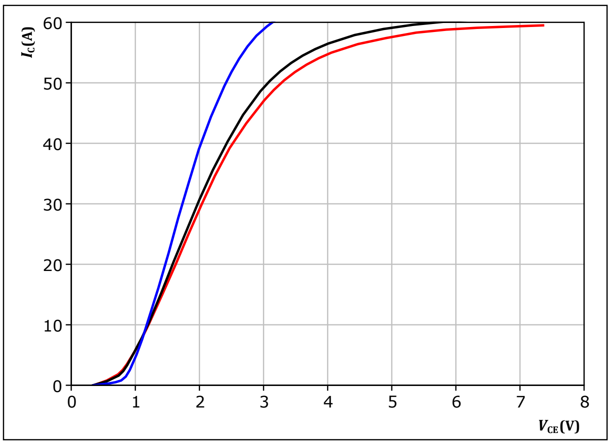
(2) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

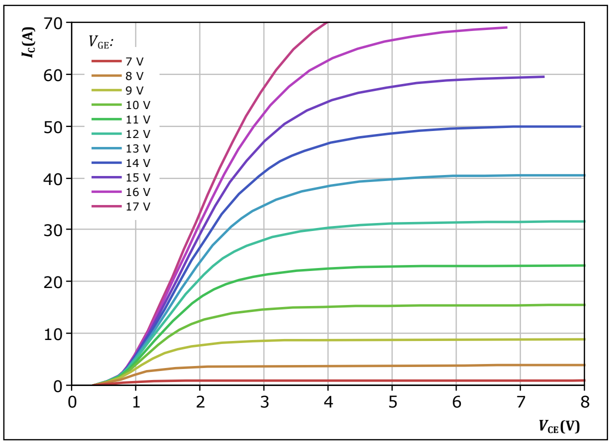


t_p =	250	µs		25 °C
V_{GE} =	15	V	T_j:	125 °C
				150 °C

figure 2. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



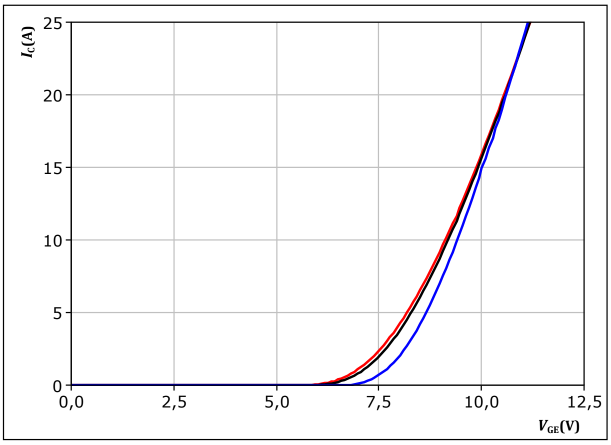
t_p =	250	µs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})

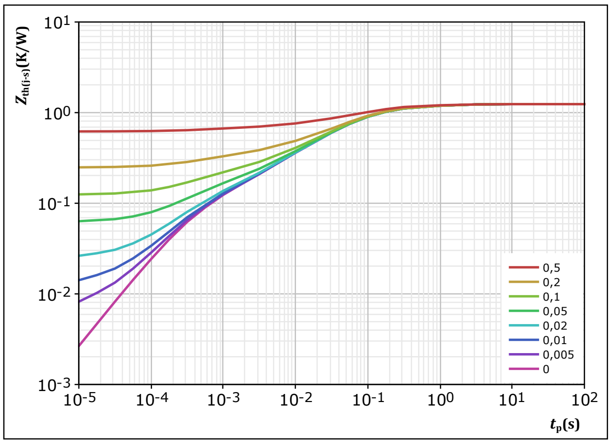


t_p =	250	µs		25 °C
V_{CE} =	10	V	T_j:	125 °C
				150 °C

figure 4. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j\text{-}s)}$ = f(t_p)



D =	t_p / T	
$R_{th(j\text{-}s)}$ =	1,24	K/W

IGBT thermal model values

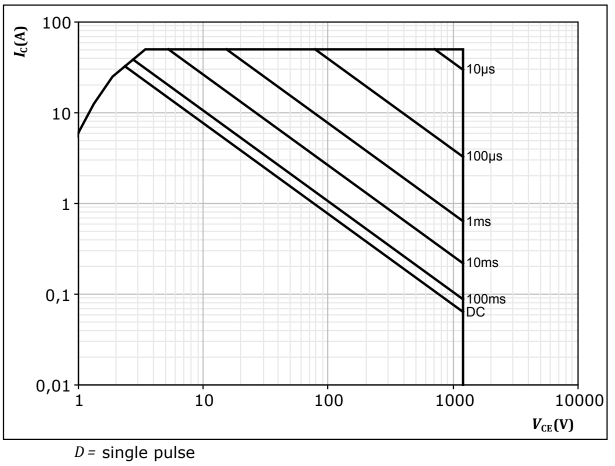
R (K/W)	τ (s)
1,03E-01	1,28E+00
2,25E-01	1,95E-01
5,52E-01	6,21E-02
2,17E-01	1,17E-02
6,67E-02	2,18E-03
7,65E-02	3,65E-04

Inverter Switch Characteristics

figure 5. **IGBT**

Safe operating area

I_C = f(V_{CE})

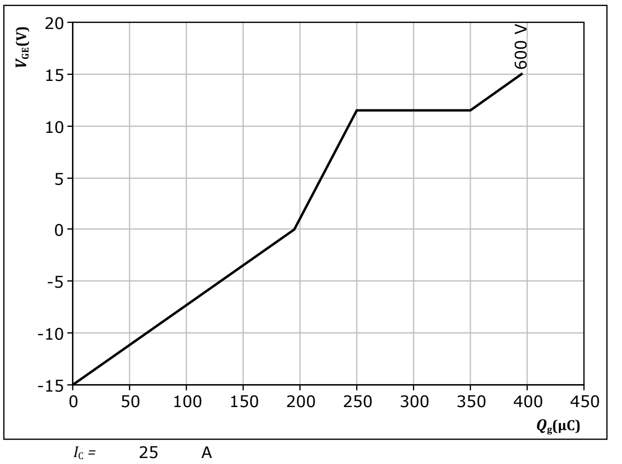


D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

figure 6. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



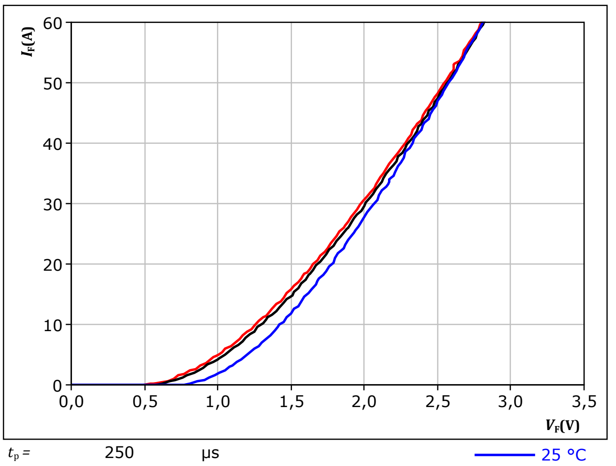
I_C =	25	A
T_j =	25	°C

Inverter Diode Characteristics

figure 7. **FWD**

Typical forward characteristics

I_F = f(V_F)



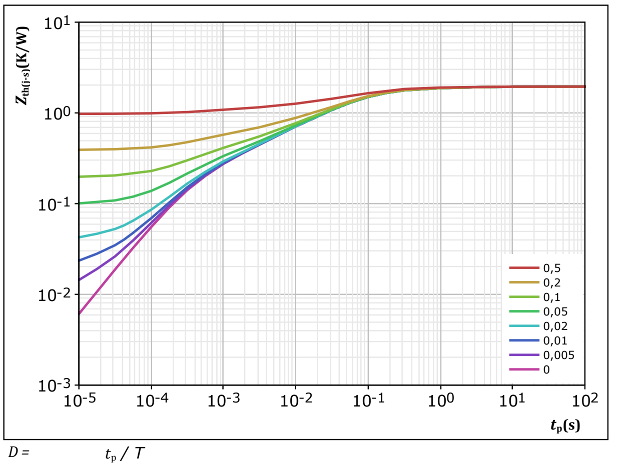
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 8. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,949 K/W

FWD thermal model values

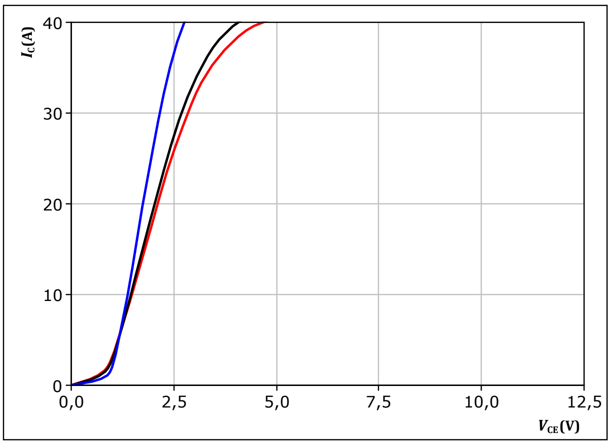
R (K/W)	τ (s)
9,75E-02	2,67E+00
2,83E-01	2,62E-01
8,34E-01	6,18E-02
3,71E-01	1,18E-02
1,87E-01	2,36E-03
1,77E-01	3,60E-04

Brake Switch Characteristics

figure 9. IGBT

Typical output characteristics

$I_C = f(V_{CE})$

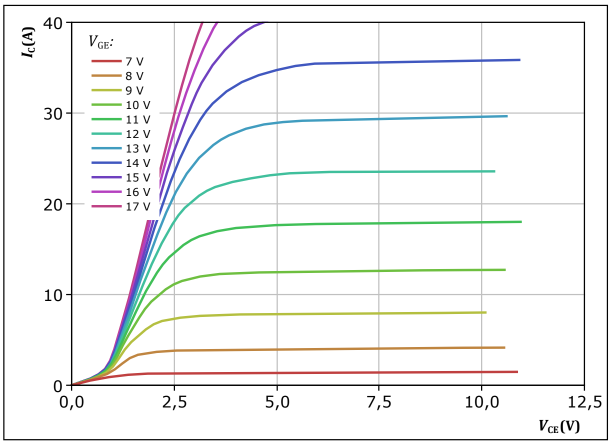


t_p =	250	μs		25 °C
V_{GE} =	15	V	T_j:	125 °C
				150 °C

figure 10. IGBT

Typical output characteristics

$I_C = f(V_{CE})$



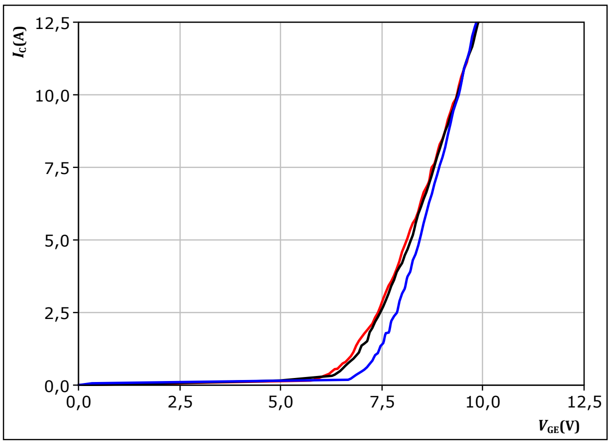
t_p =	250	μs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 11. IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$

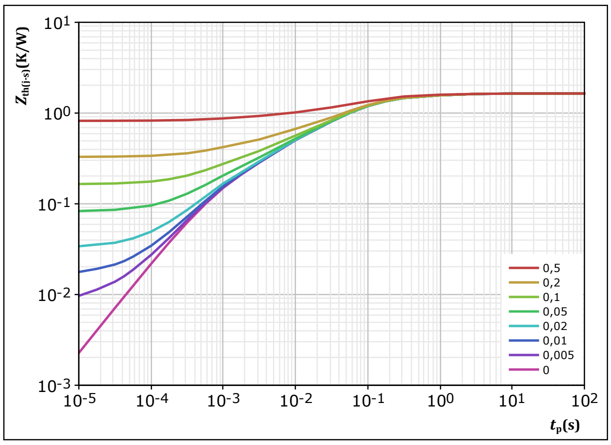


t_p =	250	μs		25 °C
V_{CE} =	60	V	T_j:	125 °C
				150 °C

figure 12. IGBT

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	1,642	K/W

IGBT thermal model values

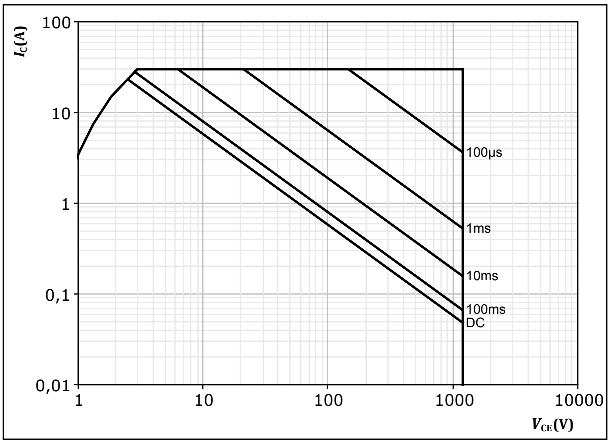
R (K/W)	τ (s)
1,33E-01	1,55E+00
3,73E-01	1,81E-01
6,89E-01	5,39E-02
3,16E-01	7,28E-03
1,30E-01	7,65E-04

Brake Switch Characteristics

figure 13. **IGBT**

Safe operating area

I_C = f(V_{CE})

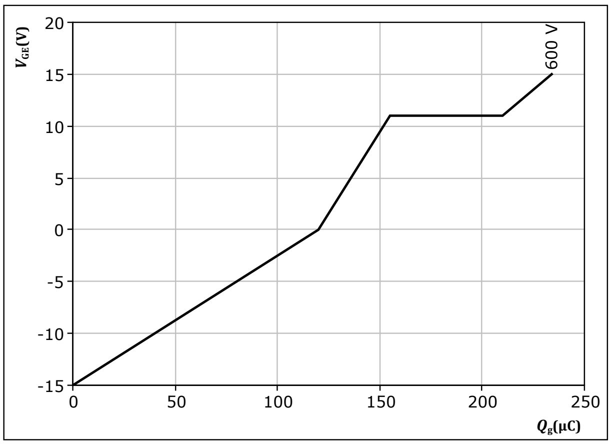


D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

figure 14. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



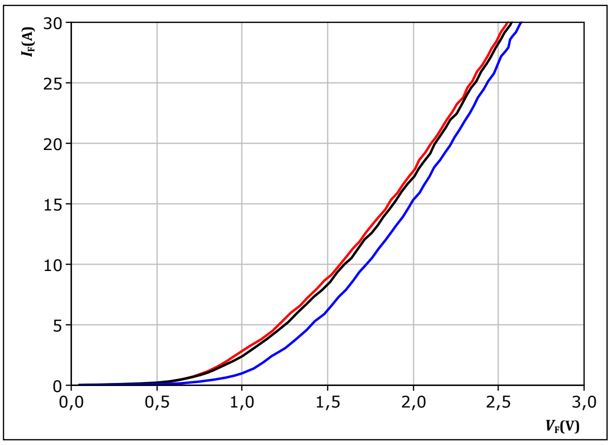
I_C =	15	A
T_j =	25	°C

Brake Diode Characteristics

figure 15. **FWD**

Typical forward characteristics

I_F = f(V_F)



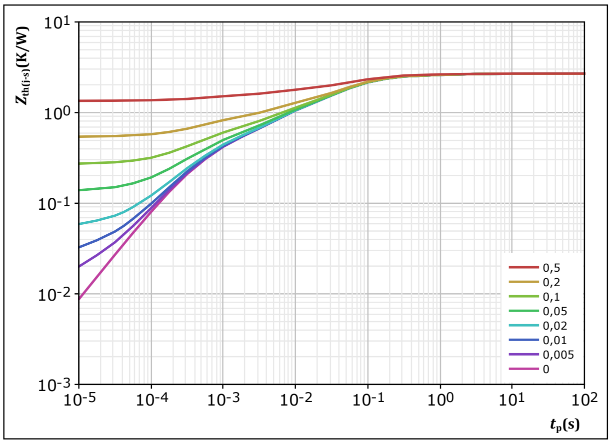
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 16. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 2,694 K/W

FWD thermal model values

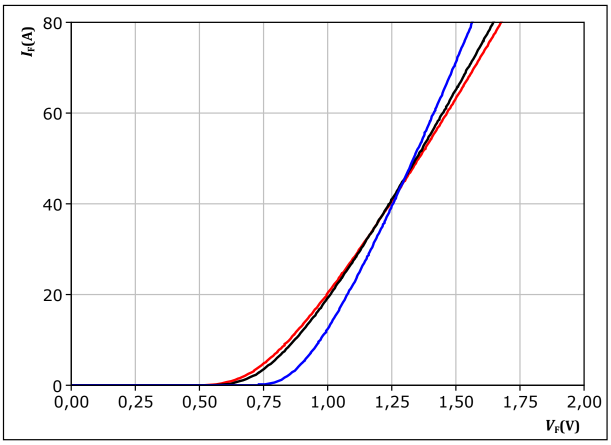
R (K/W)	τ (s)
1,39E-01	2,00E+00
6,02E-01	1,47E-01
1,12E+00	4,18E-02
5,14E-01	4,71E-03
3,24E-01	4,38E-04

Rectifier Diode Characteristics

figure 17. **Rectifier**

Typical forward characteristics

$I_F = f(V_F)$



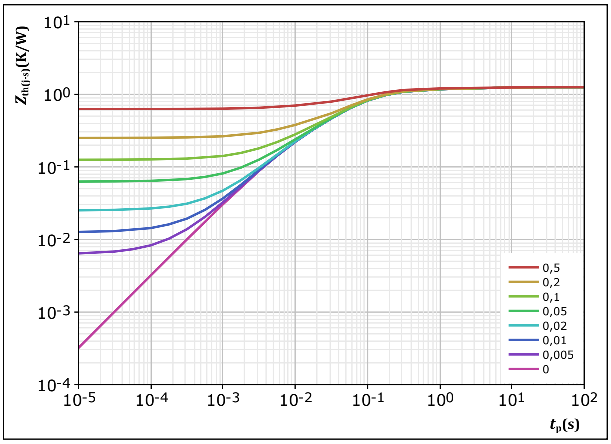
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 18. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$

$R_{th(j-s)}$ = 1,254 K/W

Rectifier thermal model values

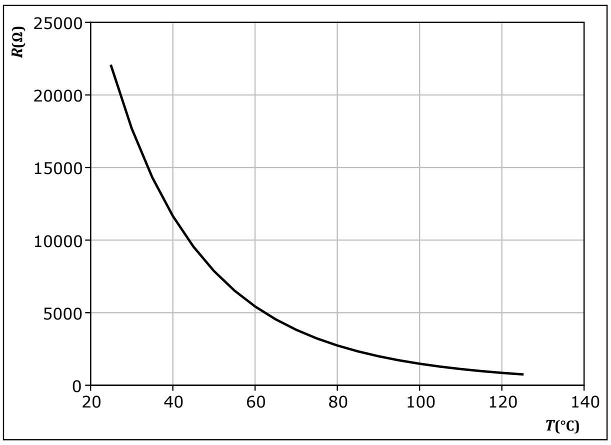
R (K/W)	τ (s)
8,00E-02	5,22E+00
1,56E-01	4,18E-01
6,95E-01	8,82E-02
2,23E-01	3,07E-02
9,97E-02	5,99E-03

Thermistor Characteristics

figure 19. **Thermistor**

Typical NTC characteristic as function of temperature

$R_T = f(T)$

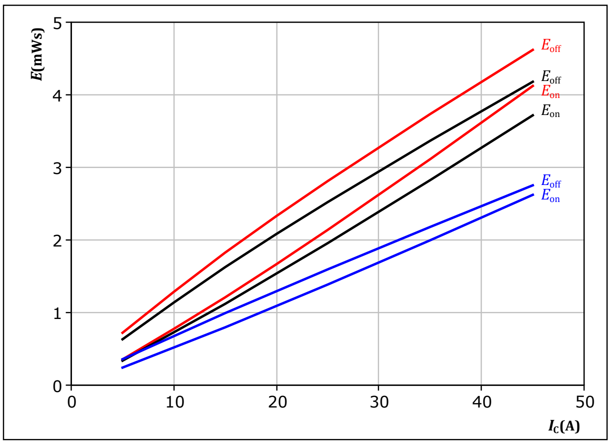


Inverter Switching Characteristics

figure 20. **IGBT**

Typical switching energy losses as a function of collector current

E = f(I_C)



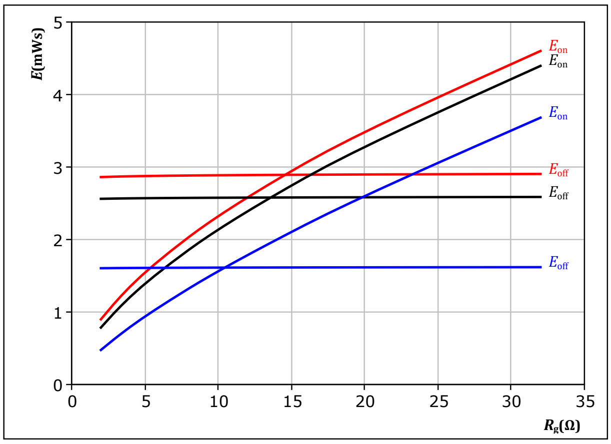
With an inductive load at

V_{CE} =	600	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
R_{gon} =	8	Ω	
R_{goff} =	8	Ω	

figure 21. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

E = f(R_g)



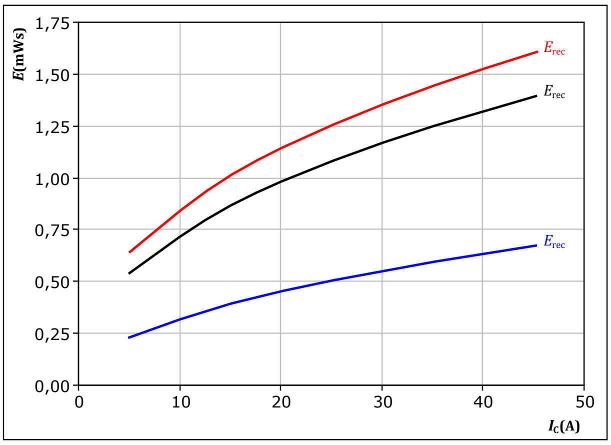
With an inductive load at

V_{CE} =	600	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
I_C =	25	A	

figure 22. **FWD**

Typical reverse recovered energy loss as a function of collector current

E_{rec} = f(I_C)



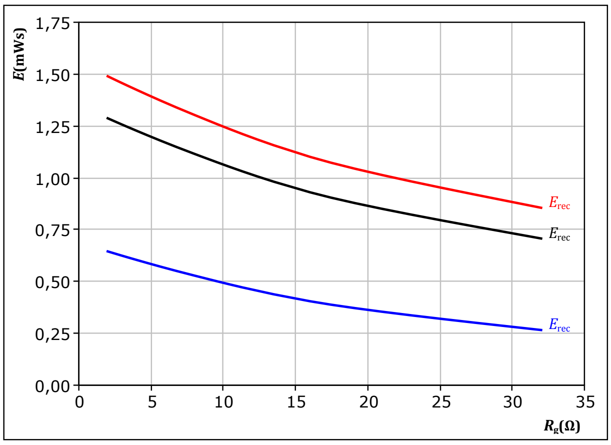
With an inductive load at

V_{CE} =	600	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
R_{gon} =	8	Ω	

figure 23. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

E_{rec} = f(R_g)



With an inductive load at

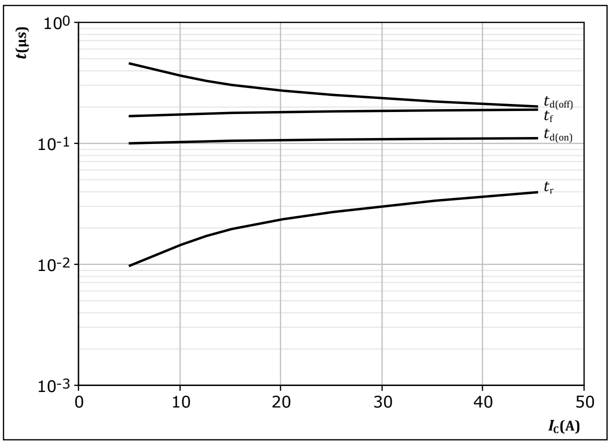
V_{CE} =	600	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
I_C =	25	A	

Inverter Switching Characteristics

figure 24. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



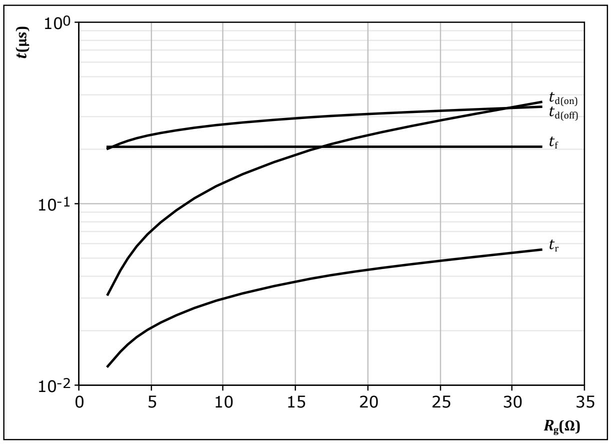
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

figure 25. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



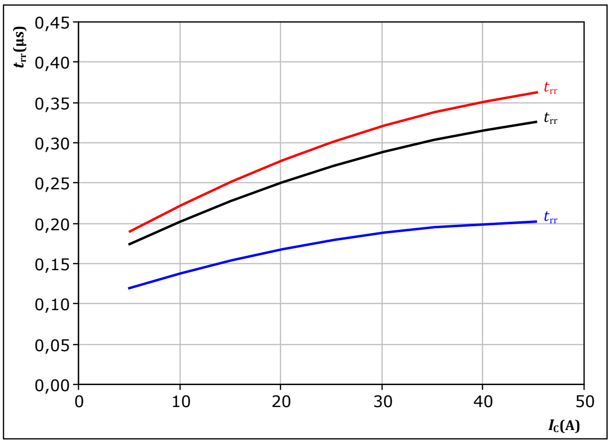
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

figure 26. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

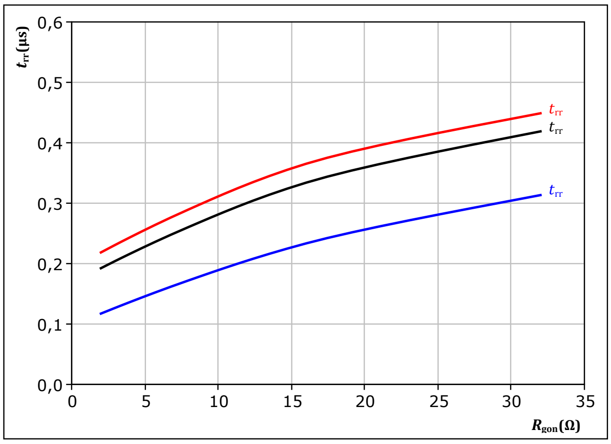
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	8	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 27. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

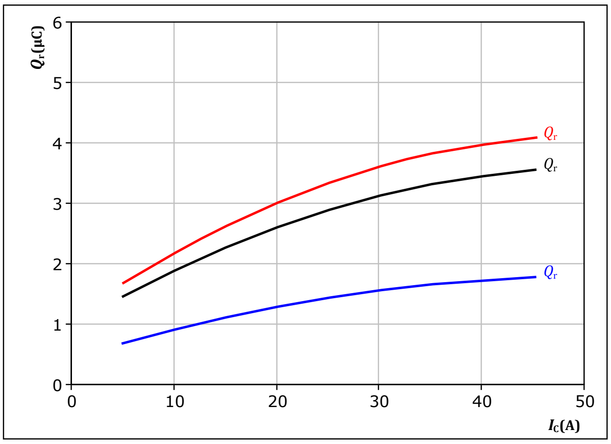
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 28. FWD

Typical recovered charge as a function of collector current

Q_r = f(I_C)



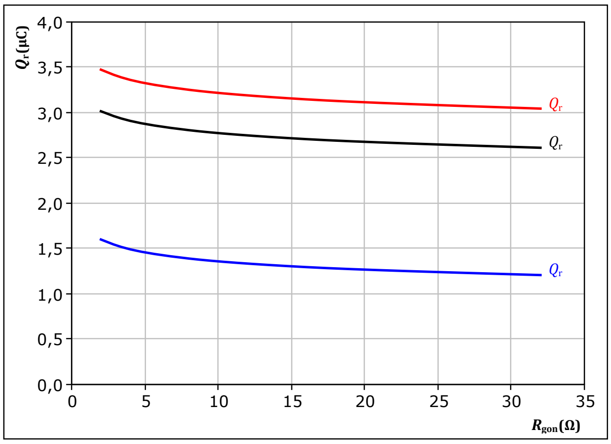
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C / 125 °C / 150 °C
V_{GE} =	±15	V		
R_{gon} =	8	Ω		

figure 29. FWD

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



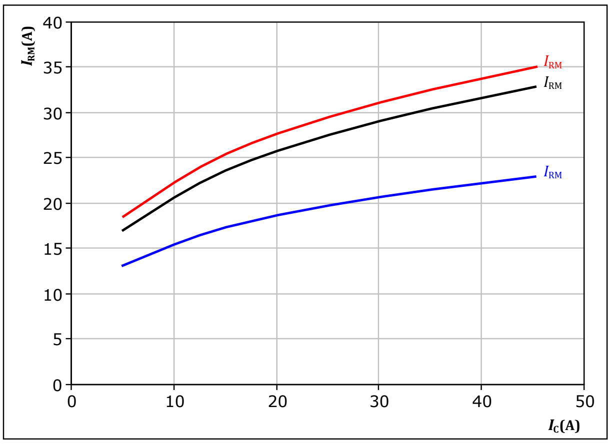
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C / 125 °C / 150 °C
V_{GE} =	±15	V		
I_C =	25	A		

figure 30. FWD

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



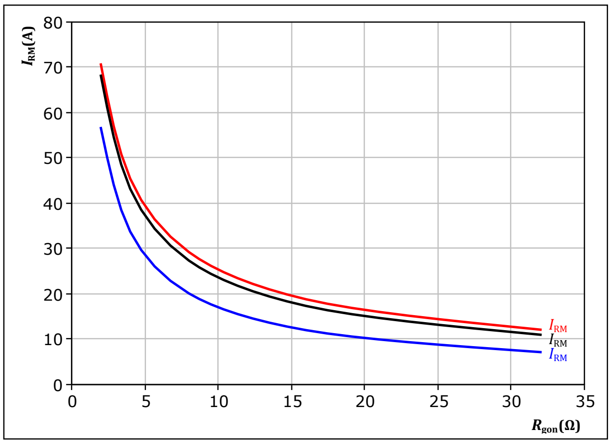
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C / 125 °C / 150 °C
V_{GE} =	±15	V		
R_{gon} =	8	Ω		

figure 31. FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

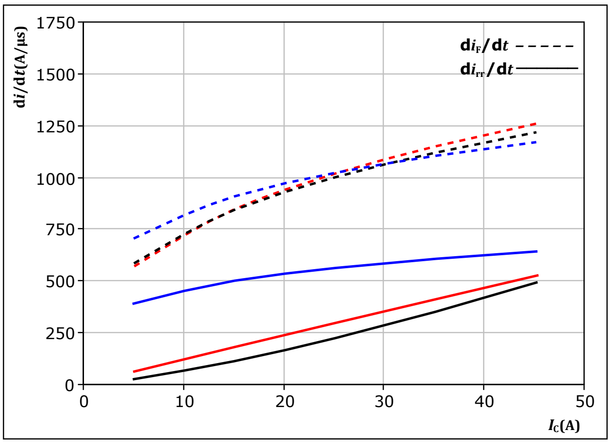
V_{CE} =	600	V	T_j:	25 °C / 125 °C / 150 °C
V_{GE} =	±15	V		
I_C =	25	A		

Inverter Switching Characteristics

figure 32. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



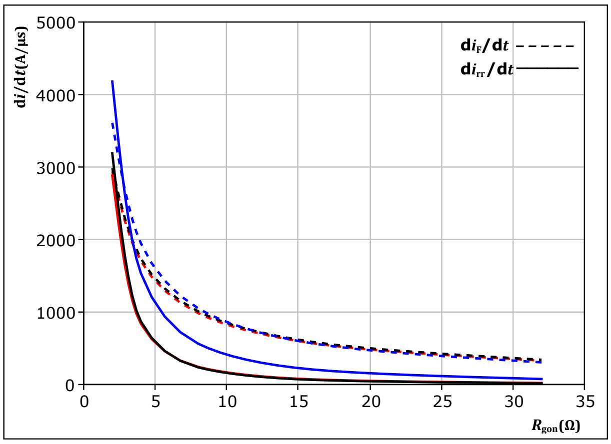
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	8	Ω		150 °C

figure 33. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



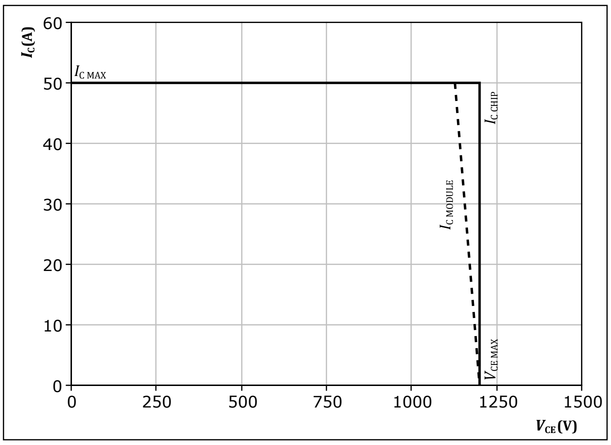
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	25	A		150 °C

figure 34. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



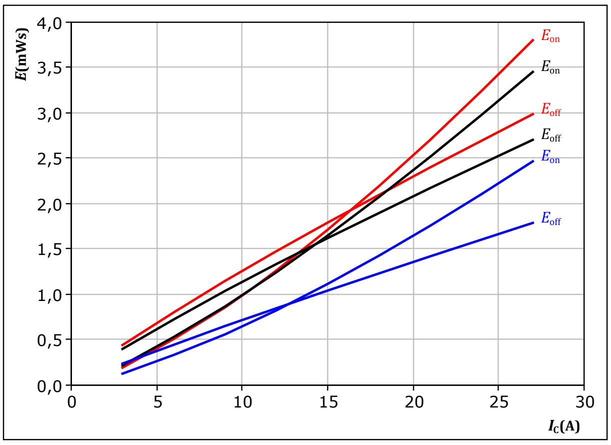
At	T_j =	150	°C
	R_{gon} =	8	Ω
	R_{goff} =	8	Ω

Brake Switching Characteristics

figure 35. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



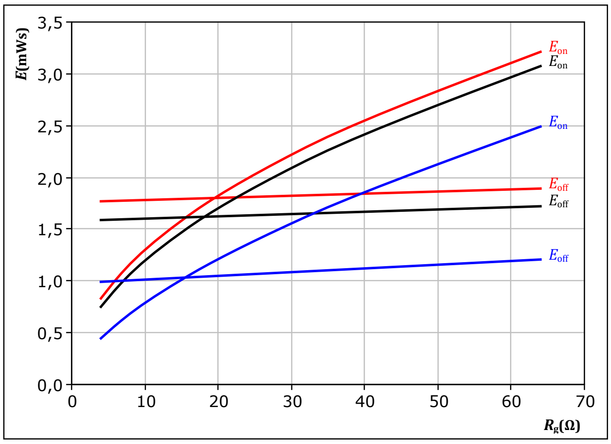
With an inductive load at

V_{CE} =	700	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	0/15	V	
R_{gon} =	16	Ω	
R_{goff} =	16	Ω	

figure 36. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



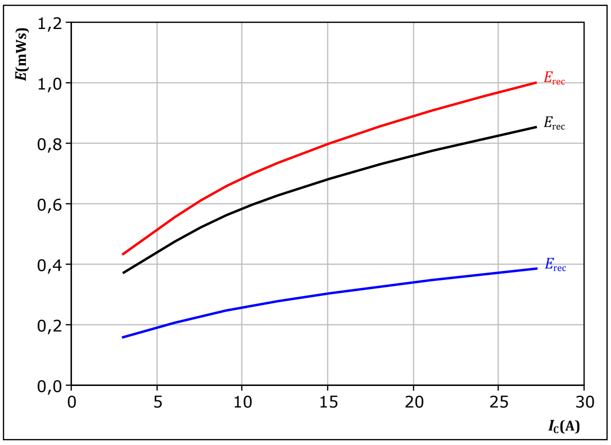
With an inductive load at

V_{CE} =	700	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	0/15	V	
I_C =	15	A	

figure 37. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



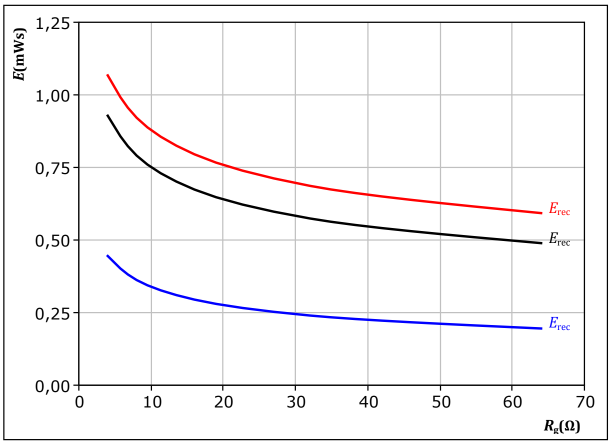
With an inductive load at

V_{CE} =	700	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	0/15	V	
R_{gon} =	16	Ω	

figure 38. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

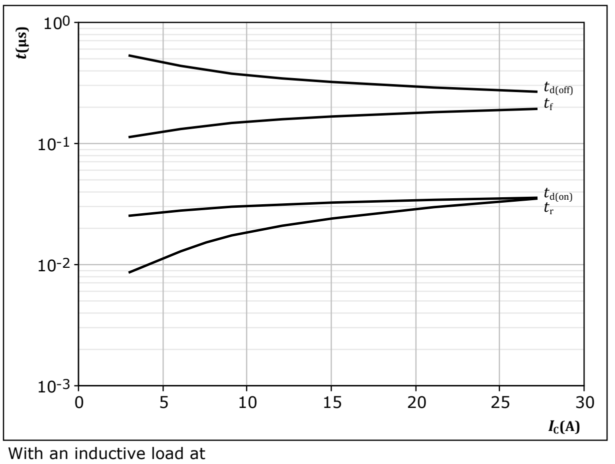
V_{CE} =	700	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	0/15	V	
I_C =	15	A	

Brake Switching Characteristics

figure 39. IGBT

Typical switching times as a function of collector current

$t = f(I_C)$



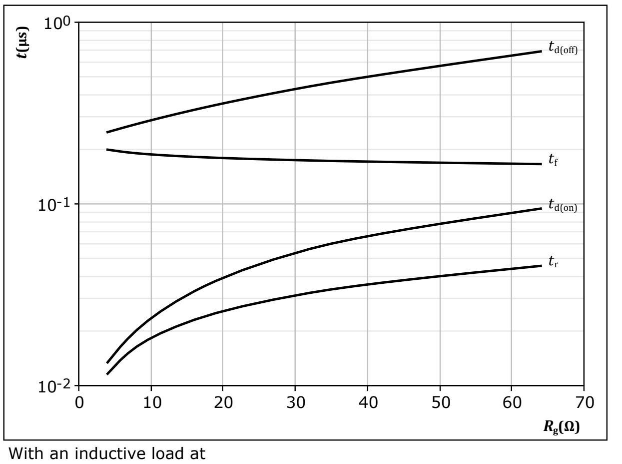
With an inductive load at

T_j =	150	°C
V_{CE} =	700	V
V_{GE} =	0/15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 40. IGBT

Typical switching times as a function of IGBT turn on gate resistor

$t = f(R_g)$



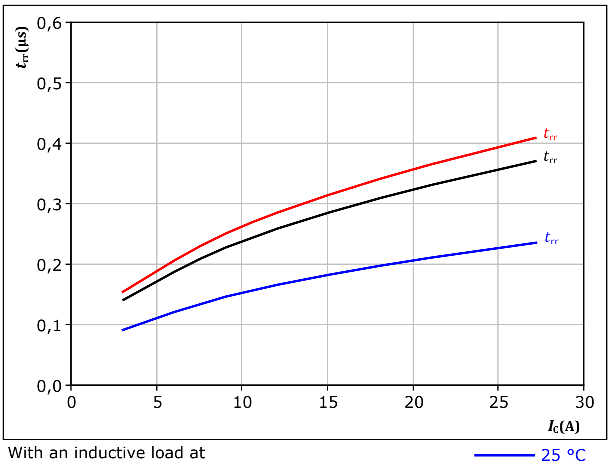
With an inductive load at

T_j =	150	°C
V_{CE} =	700	V
V_{GE} =	0/15	V
I_C =	15	A

figure 41. FWD

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



With an inductive load at

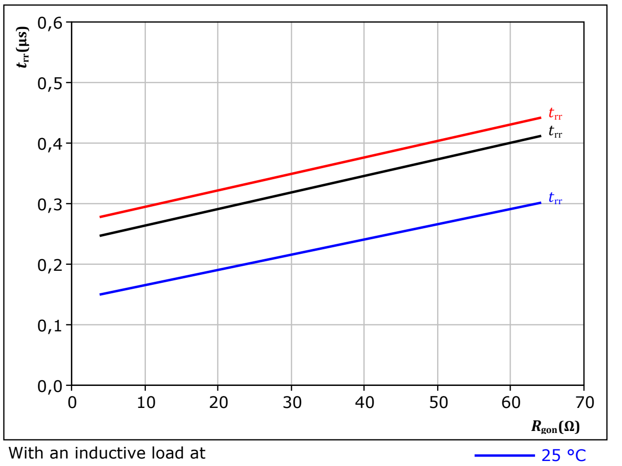
V_{CE} =	700	V
V_{GE} =	0/15	V
R_{gon} =	16	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 42. FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



With an inductive load at

V_{CE} =	700	V
V_{GE} =	0/15	V
I_C =	15	A

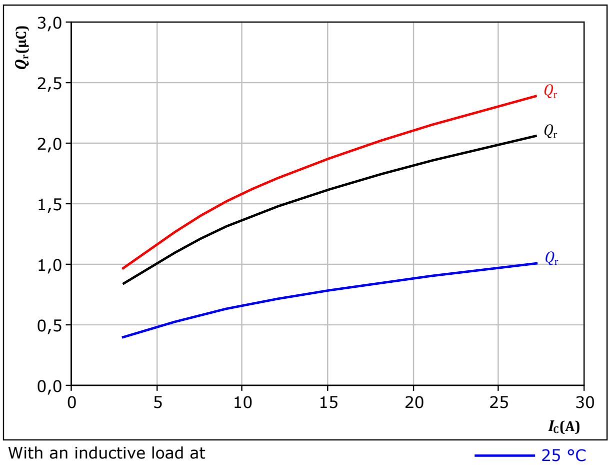
T_j: 25 °C, 125 °C, 150 °C

Brake Switching Characteristics

figure 43. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



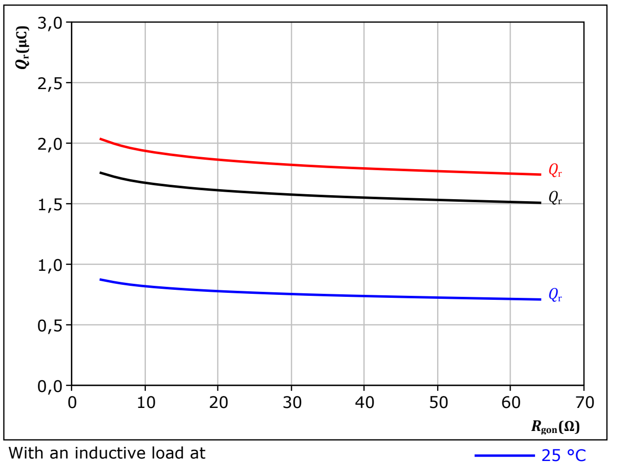
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 44. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



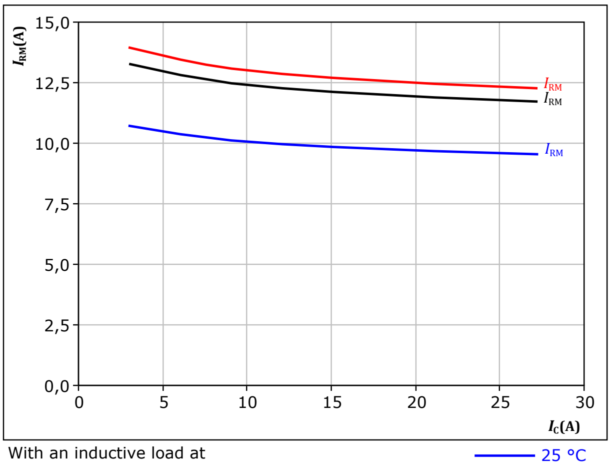
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	15	A		150 °C

figure 45. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



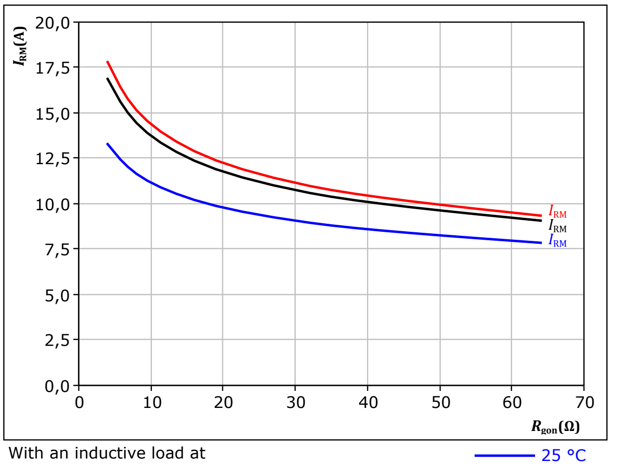
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 46. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

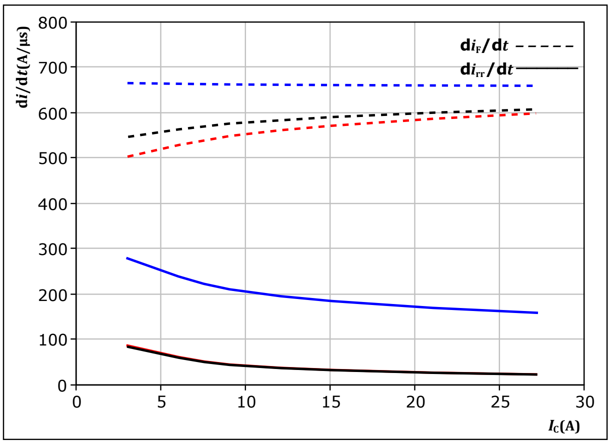
V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	15	A		150 °C

Brake Switching Characteristics

figure 47. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



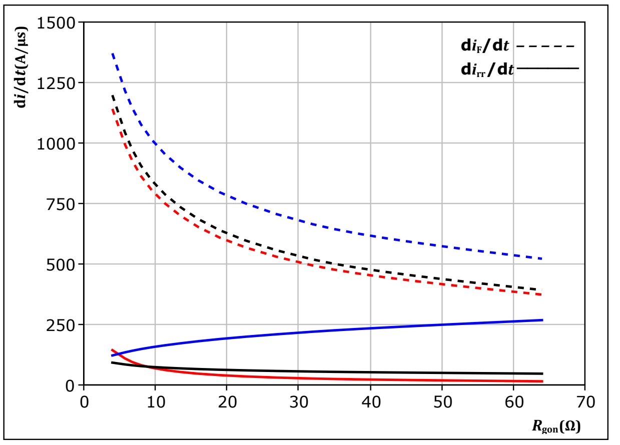
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 48. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



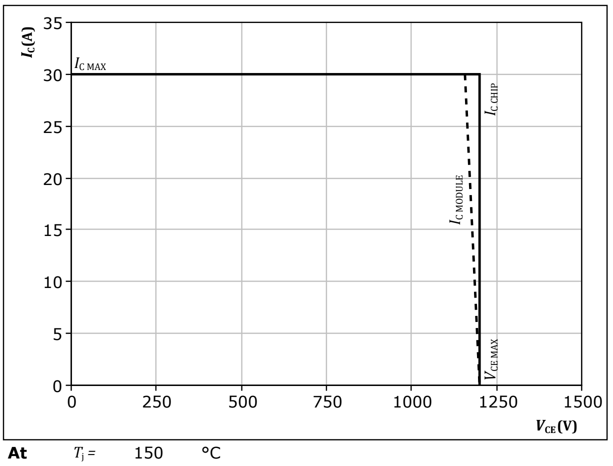
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	15	A		150 °C

figure 49. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At	T_j =	150	°C
	R_{gon} =	16	Ω
	R_{goff} =	16	Ω

Switching Definitions

figure 50. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} = integrating time for E_{off})

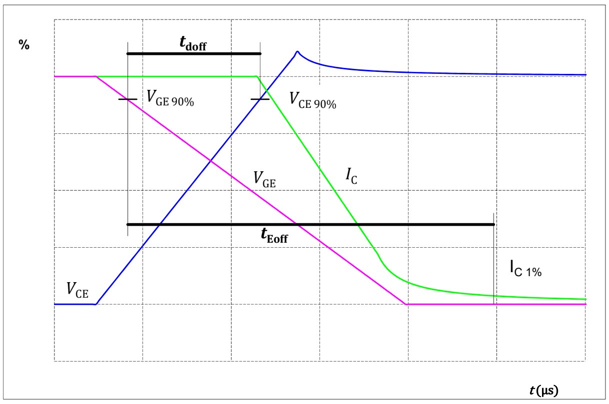


figure 51. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

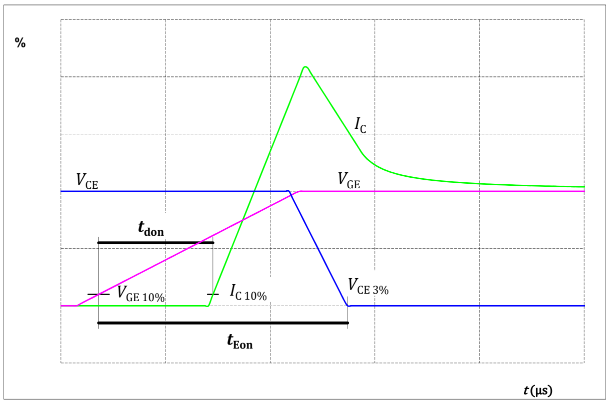


figure 52. **IGBT**

Turn-off Switching Waveforms & definition of t_f

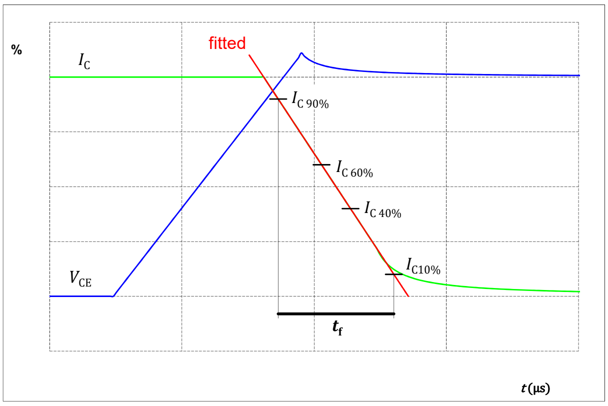
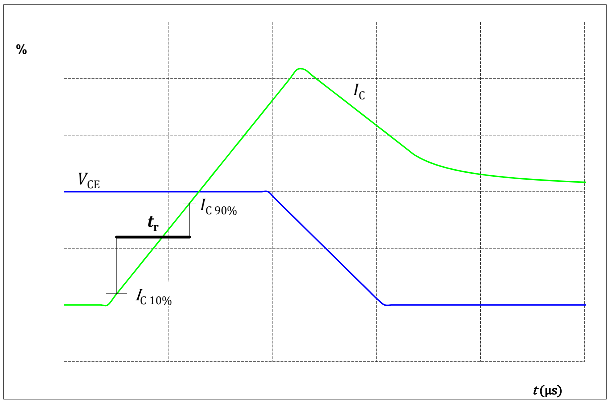


figure 53. **IGBT**

Turn-on Switching Waveforms & definition of t_r



Switching Definitions

figure 54. FWD

Turn-off Switching Waveforms & definition of t_{rr}

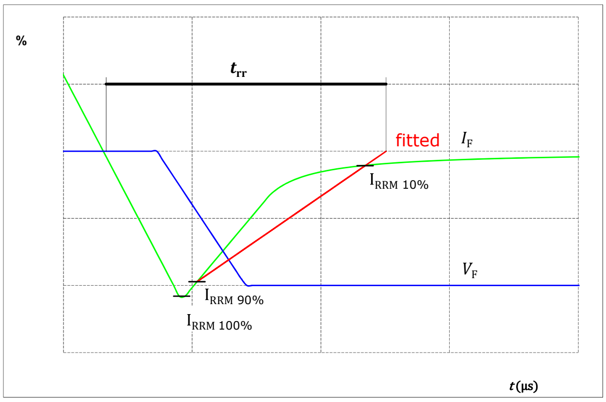
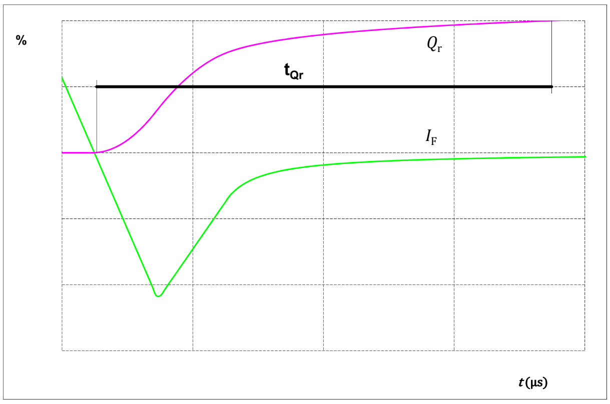


figure 55. FWD

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Ordering Code

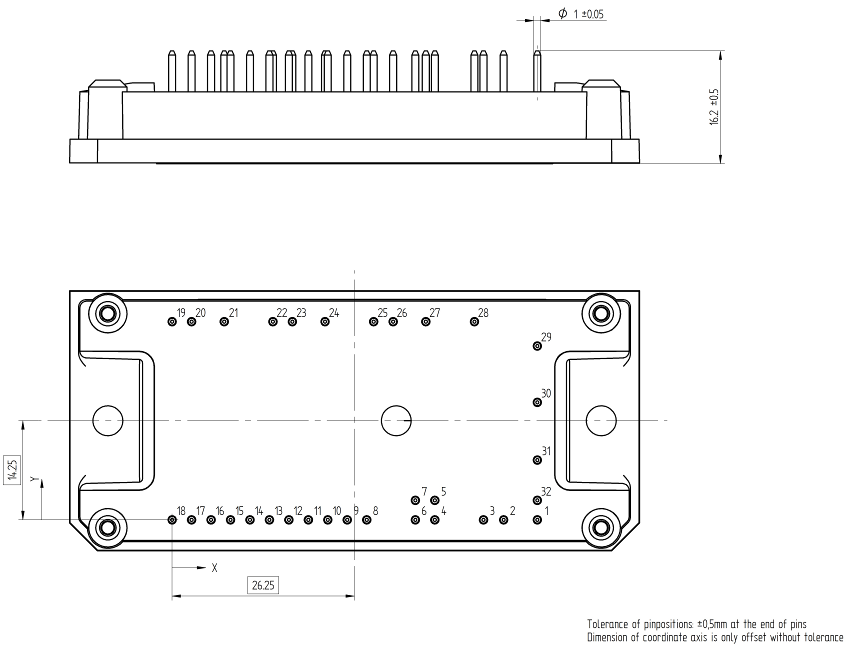
Version	Ordering Code
Without thermal paste	10-FY12PMA025I7-P588A98
With thermal paste (5,2 W/mK, PTM6000HV)	10-FY12PMA025I7-P588A98-/7/
With thermal paste (3,4 W/mK, PSX-P7)	10-FY12PMA025I7-P588A98-/3/

Marking

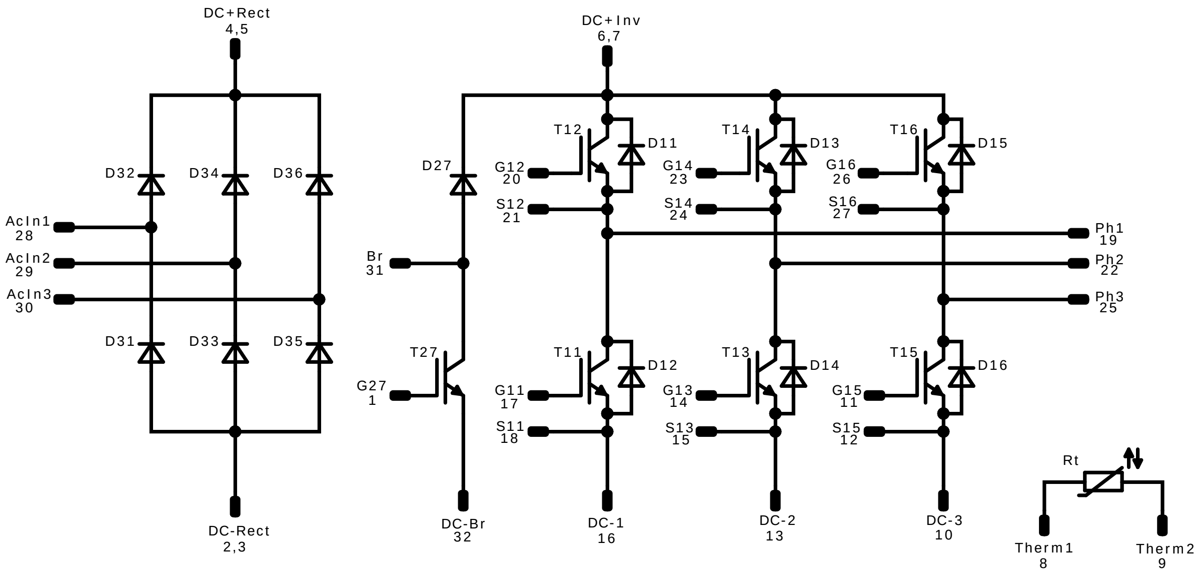
Text	**Name**		**Date code**	**UL & VIN**	**Lot**	**Serial**
	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

Pin table [mm]			
Pin	X	Y	Function
1	52,55	0	G27
2	47,7	0	DC-Rect
3	44,8	0	DC-Rect
4	37,8	0	DC+Rect
5	37,8	2,8	DC+Rect
6	35	0	DC+Inv
7	35	2,8	DC+Inv
8	28	0	Therm1
9	25,2	0	Therm2
10	22,4	0	DC-3
11	19,6	0	G15
12	16,8	0	S15
13	14	0	DC-2
14	11,2	0	G13
15	8,4	0	S13
16	5,6	0	DC-1
17	2,8	0	G11
18	0	0	S11
19	0	28,5	Ph1
20	2,8	28,5	G12
21	7,5	28,5	S12
22	14,5	28,5	Ph2
23	17,3	28,5	G14
24	22	28,5	S14
25	29	28,5	Ph3
26	31,8	28,5	G16
27	36,5	28,5	S16
28	43,5	28,5	ACIn1
29	52,55	25	ACIn2
30	52,55	16,9	ACIn3
31	52,55	8,6	Br
32	52,55	2,8	DC-Br



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T16, T15, T16	IGBT	1200 V	25 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	1200 V	21 A	Inverter Diode	
T27	IGBT	1200 V	15 A	Brake Switch	
D27	FWD	1200 V	11 A	Brake Diode	
D31, D32, D33, D34, D35, D36	Rectifier	1600 V	28 A	Rectifier Diode	
Rt	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 1 packages see vincotech.com website.

Package data
Package data for *flow* 1 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-FY12PMA025I7-P588A98-D1-14	20 Aug. 2022		